



Welcome to [E-XFL.COM](#)

Understanding [Embedded - Microprocessors](#)

Embedded microprocessors are specialized computing chips designed to perform specific tasks within an embedded system. Unlike general-purpose microprocessors found in personal computers, embedded microprocessors are tailored for dedicated functions within larger systems, offering optimized performance, efficiency, and reliability. These microprocessors are integral to the operation of countless electronic devices, providing the computational power necessary for controlling processes, handling data, and managing communications.

Applications of [Embedded - Microprocessors](#)

Embedded microprocessors are utilized across a broad spectrum of applications, making them indispensable in

Details

Product Status	Obsolete
Core Processor	PowerPC e300
Number of Cores/Bus Width	1 Core, 32-Bit
Speed	400MHz
Co-Processors/DSP	-
RAM Controllers	DDR, DDR2
Graphics Acceleration	No
Display & Interface Controllers	-
Ethernet	10/100/1000Mbps (3)
SATA	-
USB	USB 2.0 + PHY (2)
Voltage - I/O	1.8V, 2.5V, 3.3V
Operating Temperature	-40°C ~ 105°C (TA)
Security Features	-
Package / Case	620-BBGA Exposed Pad
Supplier Device Package	620-HBGA (29x29)
Purchase URL	https://www.e-xfl.com/product-detail/nxp-semiconductors/mpc8343cvragd

- Address translation units for address mapping between host and peripheral
- Dual address cycle for target
- Internal configuration registers accessible from PCI
- Security engine is optimized to handle all the algorithms associated with IPSec, SSL/TLS, SRTP, IEEE Std. 802.11i®, iSCSI, and IKE processing. The security engine contains four crypto-channels, a controller, and a set of crypto execution units (EUs):
 - Public key execution unit (PKEU) :
 - RSA and Diffie-Hellman algorithms
 - Programmable field size up to 2048 bits
 - Elliptic curve cryptography
 - F2m and F(p) modes
 - Programmable field size up to 511 bits
 - Data encryption standard (DES) execution unit (DEU)
 - DES and 3DES algorithms
 - Two key (K1, K2) or three key (K1, K2, K3) for 3DES
 - ECB and CBC modes for both DES and 3DES
 - Advanced encryption standard unit (AESU)
 - Implements the Rijndael symmetric-key cipher
 - Key lengths of 128, 192, and 256 bits
 - ECB, CBC, CCM, and counter (CTR) modes
 - XOR parity generation accelerator for RAID applications
 - ARC four execution unit (AFEU)
 - Stream cipher compatible with the RC4 algorithm
 - 40- to 128-bit programmable key
 - Message digest execution unit (MDEU)
 - SHA with 160-, 224-, or 256-bit message digest
 - MD5 with 128-bit message digest
 - HMAC with either algorithm
 - Random number generator (RNG)
 - Four crypto-channels, each supporting multi-command descriptor chains
 - Static and/or dynamic assignment of crypto-execution units through an integrated controller
 - Buffer size of 256 bytes for each execution unit, with flow control for large data sizes
- Universal serial bus (USB) dual role controller
 - USB on-the-go mode with both device and host functionality
 - Complies with USB specification Rev. 2.0
 - Can operate as a stand-alone USB device
 - One upstream facing port
 - Six programmable USB endpoints

- Misaligned transfer capability
- Data chaining and direct mode
- Interrupt on completed segment and chain
- DUART
 - Two 4-wire interfaces (RxD, TxD, RTS, CTS)
 - Programming model compatible with the original 16450 UART and the PC16550D
- Serial peripheral interface (SPI) for master or slave
- General-purpose parallel I/O (GPIO)
 - 39 parallel I/O pins multiplexed on various chip interfaces
- System timers
 - Periodic interrupt timer
 - Real-time clock
 - Software watchdog timer
 - Eight general-purpose timers
- Designed to comply with IEEE Std. 1149.1™, JTAG boundary scan
- Integrated PCI bus and SDRAM clock generation

2 Electrical Characteristics

This section provides the AC and DC electrical specifications and thermal characteristics for the MPC8343EA. The device is currently targeted to these specifications. Some of these specifications are independent of the I/O cell, but are included for a more complete reference. These are not purely I/O buffer design specifications.

2.1 Overall DC Electrical Characteristics

This section covers the ratings, conditions, and other characteristics.

2.1.1 Absolute Maximum Ratings

Table 1 provides the absolute maximum ratings.

Table 1. Absolute Maximum Ratings¹

Parameter	Symbol	Max Value	Unit	Notes
Core supply voltage	V_{DD}	–0.3 to 1.32	V	—
PLL supply voltage	AV_{DD}	–0.3 to 1.32	V	—
DDR and DDR2 DRAM I/O voltage	GV_{DD}	–0.3 to 2.75 –0.3 to 1.98	V	—
Three-speed Ethernet I/O, MII management voltage	LV_{DD}	–0.3 to 3.63	V	—
PCI, local bus, DUART, system control and power management, I ² C, and JTAG I/O voltage	OV_{DD}	–0.3 to 3.63	V	—

Table 2. Recommended Operating Conditions (continued)

Parameter	Symbol	Recommended Value	Unit	Notes
PCI, local bus, DUART, system control and power management, I ² C, and JTAG I/O voltage	OV _{DD}	3.3 V ± 330 mV	V	—

Note:

¹ GV_{DD}, LV_{DD}, OV_{DD}, AV_{DD}, and V_{DD} must track each other and must vary in the same direction—either in the positive or negative direction.

Figure 2 shows the undershoot and overshoot voltages at the interfaces of the MPC8343EA.

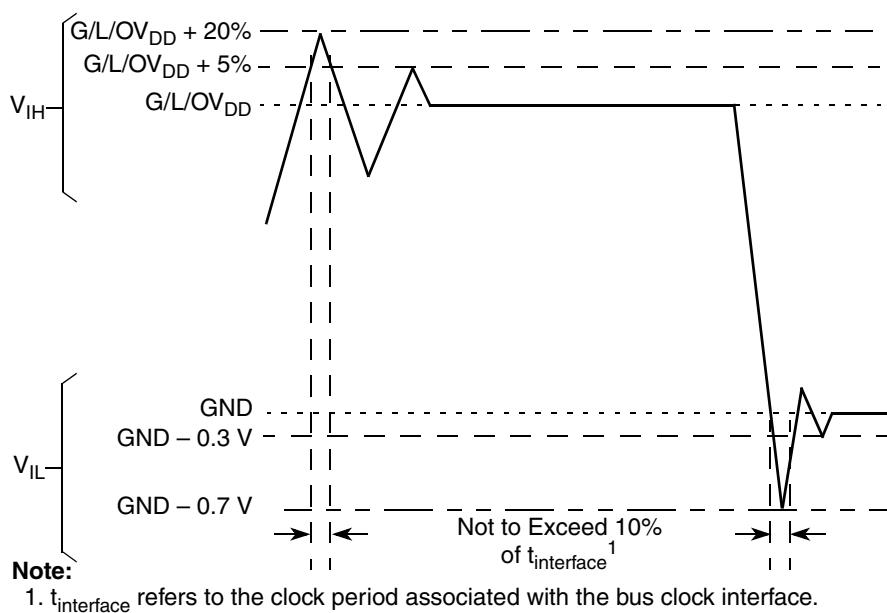

Figure 2. Overshoot/Undershoot Voltage for GV_{DD}/OV_{DD}/LV_{DD}

Table 19. DDR and DDR2 SDRAM Input AC Timing Specifications (continued)

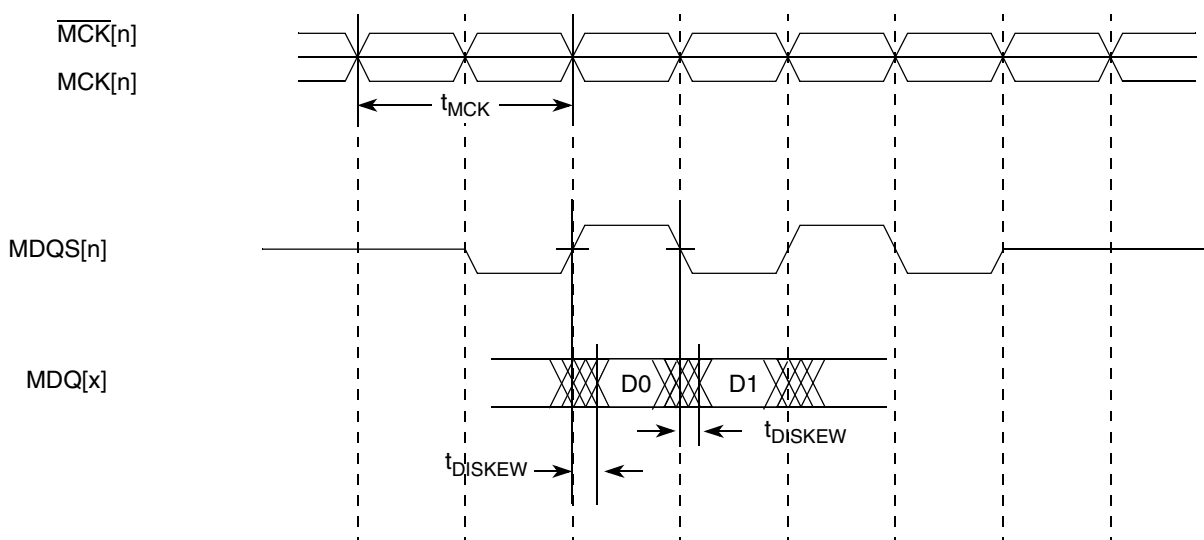
At recommended operating conditions with GV_{DD} of (1.8 or 2.5 V) \pm 5%.

Parameter	Symbol	Min	Max	Unit	Notes
266 MHz		-750	750		—
200 MHz		-750	750		—

Notes:

1. t_{CISKEW} represents the total amount of skew consumed by the controller between MDQS[n] and any corresponding bit that will be captured with MDQS[n]. This should be subtracted from the total timing budget.
2. The amount of skew that can be tolerated from MDQS to a corresponding MDQ signal is called t_{DISKEW} . This can be determined by the equation: $t_{DISKEW} = \pm (T/4 - \text{abs}(t_{CISKEW}))$; where T is the clock period and $\text{abs}(t_{CISKEW})$ is the absolute value of t_{CISKEW} .
3. This specification applies only to the DDR interface.

Figure 5 illustrates the DDR input timing diagram showing the t_{DISKEW} timing parameter.


Figure 5. DDR Input Timing Diagram

6.2.2 DDR and DDR2 SDRAM Output AC Timing Specifications

Table 20 shows the DDR and DDR2 output AC timing specifications.

Table 20. DDR and DDR2 SDRAM Output AC Timing Specifications

At recommended operating conditions with GV_{DD} of (1.8 or 2.5 V) \pm 5%.

Parameter	Symbol ¹	Min	Max	Unit	Notes
MCK[n] cycle time, (MCK[n]/ $\overline{\text{MCK[n]}}$ crossing)	t_{MCK}	7.5	10	ns	2
ADDR/CMD/MODT output setup with respect to MCK	t_{DDKHAS}			ns	3
400 MHz		1.95	—		
333 MHz		2.40	—		
266 MHz		3.15	—		
200 MHz		4.20	—		

Table 20. DDR and DDR2 SDRAM Output AC Timing Specifications (continued)

At recommended operating conditions with GV_{DD} of $(1.8 \text{ or } 2.5 \text{ V}) \pm 5\%$.

Parameter	Symbol ¹	Min	Max	Unit	Notes
MDQS epilogue end	t_{DDKHME}	-0.6	0.6	ns	6

Notes:

1. The symbols for timing specifications follow the pattern of $t_{(\text{first two letters of functional block})(\text{signal})(\text{state})(\text{reference})(\text{state})}$ for inputs and $t_{(\text{first two letters of functional block})(\text{reference})(\text{state})(\text{signal})(\text{state})}$ for outputs. Output hold time can be read as DDR timing (DD) from the rising or falling edge of the reference clock (KH or KL) until the output goes invalid (AX or DX). For example, t_{DDKHAS} symbolizes DDR timing (DD) for the time t_{MCK} memory clock reference (K) goes from the high (H) state until outputs (A) are set up (S) or output valid time. Also, t_{DDKLDX} symbolizes DDR timing (DD) for the time t_{MCK} memory clock reference (K) goes low (L) until data outputs (D) are invalid (X) or data output hold time.
2. All MCK/ \overline{MCK} referenced measurements are made from the crossing of the two signals $\pm 0.1 \text{ V}$.
3. ADDR/CMD includes all DDR SDRAM output signals except MCK/ \overline{MCK} , \overline{MCS} , and MDQ/MECC/MDM/MDQS. For the ADDR/CMD setup and hold specifications, it is assumed that the clock control register is set to adjust the memory clocks by 1/2 applied cycle.
4. t_{DDKHHM} follows the symbol conventions described in note 1. For example, t_{DDKHHM} describes the DDR timing (DD) from the rising edge of the MCK(n) clock (KH) until the MDQS signal is valid (MH). t_{DDKHHM} can be modified through control of the DQSS override bits in the TIMING_CFG_2 register and is typically set to the same delay as the clock adjust in the CLK_CNTL register. The timing parameters listed in the table assume that these two parameters are set to the same adjustment value. See the *MPC8349EA PowerQUICC II Pro Integrated Host Processor Family Reference Manual* for the timing modifications enabled by use of these bits.
5. Determined by maximum possible skew between a data strobe (MDQS) and any corresponding bit of data (MDQ), ECC (MECC), or data mask (MDM). The data strobe should be centered inside the data eye at the pins of the microprocessor.
6. All outputs are referenced to the rising edge of MCK(n) at the pins of the microprocessor. Note that t_{DDKHMP} follows the symbol conventions described in note 1.

Figure 6 shows the DDR SDRAM output timing for the MCK to MDQS skew measurement (t_{DDKHHM}).

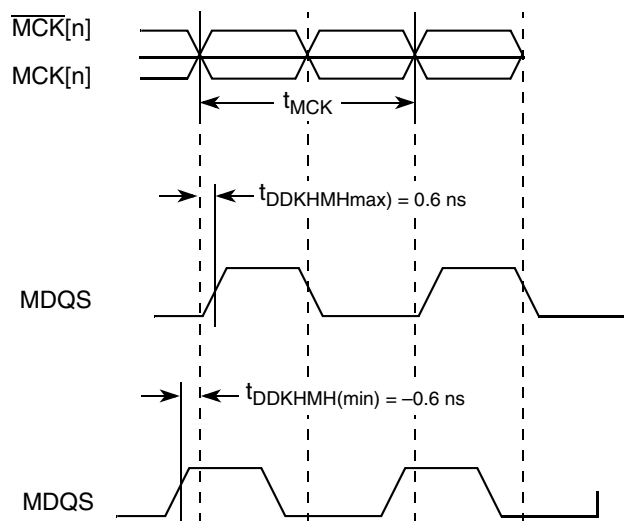

Figure 6. Timing Diagram for t_{DDKHHM}

Table 28. MII Management DC Electrical Characteristics Powered at 2.5 V (continued)

Parameter	Symbol	Conditions	Min	Max	Unit
Input high current	I_{IH}	$V_{IN}^1 = LV_{DD}$	—	10	μA
Input low current	I_{IL}	$V_{IN} = LV_{DD}$	–15	—	μA

Note:

1. The symbol V_{IN} , in this case, represents the LV_{IN} symbol referenced in [Table 1](#) and [Table 2](#).

Table 29. MII Management DC Electrical Characteristics Powered at 3.3 V

Parameter	Symbol	Conditions		Min	Max	Unit
Supply voltage (3.3 V)	LV_{DD}	—		2.97	3.63	V
Output high voltage	V_{OH}	$I_{OH} = -1.0 \text{ mA}$	$LV_{DD} = \text{Min}$	2.10	$LV_{DD} + 0.3$	V
Output low voltage	V_{OL}	$I_{OL} = 1.0 \text{ mA}$	$LV_{DD} = \text{Min}$	GND	0.50	V
Input high voltage	V_{IH}	—		2.00	—	V
Input low voltage	V_{IL}	—		—	0.80	V
Input high current	I_{IH}	$LV_{DD} = \text{Max}$	$V_{IN}^1 = 2.1 \text{ V}$	—	40	μA
Input low current	I_{IL}	$LV_{DD} = \text{Max}$	$V_{IN} = 0.5 \text{ V}$	–600	—	μA

Note:

1. The symbol V_{IN} , in this case, represents the LV_{IN} symbol referenced in [Table 1](#) and [Table 2](#).

8.3.2 MII Management AC Electrical Specifications

[Table 30](#) provides the MII management AC timing specifications.

Table 30. MII Management AC Timing Specifications

At recommended operating conditions with LV_{DD} is 3.3 V \pm 10% or 2.5 V \pm 5%.

Parameter/Condition	Symbol ¹	Min	Typ	Max	Unit	Notes
MDC frequency	f_{MDC}	—	2.5	—	MHz	2
MDC period	t_{MDC}	—	400	—	ns	—
MDC clock pulse width high	t_{MDCH}	32	—	—	ns	—
MDC to MDIO delay	t_{MDKHDX}	10	—	70	ns	3
MDIO to MDC setup time	t_{MDDVKH}	5	—	—	ns	—
MDIO to MDC hold time	t_{MDDXKH}	0	—	—	ns	—
MDC rise time	t_{MDCR}	—	—	10	ns	—

Table 30. MII Management AC Timing Specifications (continued)

At recommended operating conditions with V_{DD} is 3.3 V \pm 10% or 2.5 V \pm 5%.

Parameter/Condition	Symbol ¹	Min	Typ	Max	Unit	Notes
MDC fall time	t_{MDHF}	—	—	10	ns	—

Notes:

1. The symbols for timing specifications follow the pattern of $t_{(first\ two\ letters\ of\ functional\ block)(signal)(state)(reference)(state)}$ for inputs and $t_{(first\ two\ letters\ of\ functional\ block)(reference)(state)(signal)(state)}$ for outputs. For example, t_{MDKHDX} symbolizes management data timing (MD) for the time t_{MDC} from clock reference (K) high (H) until data outputs (D) are invalid (X) or data hold time. Also, t_{MDDVKH} symbolizes management data timing (MD) with respect to the time data input signals (D) reach the valid state (V) relative to the t_{MDC} clock reference (K) going to the high (H) state or setup time. For rise and fall times, the latter convention is used with the appropriate letter: R (rise) or F (fall).
2. This parameter is dependent on the csb_clk speed (that is, for a csb_clk of 267 MHz, the maximum frequency is 8.3 MHz and the minimum frequency is 1.2 MHz; for a csb_clk of 375 MHz, the maximum frequency is 11.7 MHz and the minimum frequency is 1.7 MHz).
3. This parameter is dependent on the csb_clk speed (that is, for a csb_clk of 267 MHz, the delay is 70 ns and for a csb_clk of 333 MHz, the delay is 58 ns).

Figure 13 shows the MII management AC timing diagram.

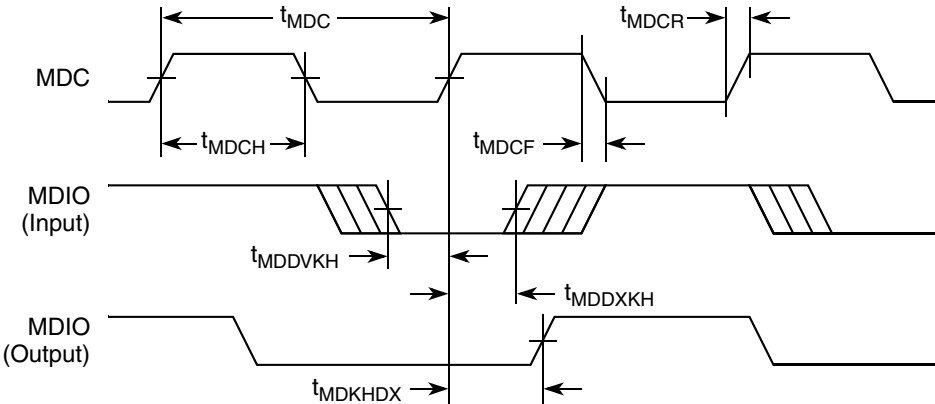


Figure 13. MII Management Interface Timing Diagram

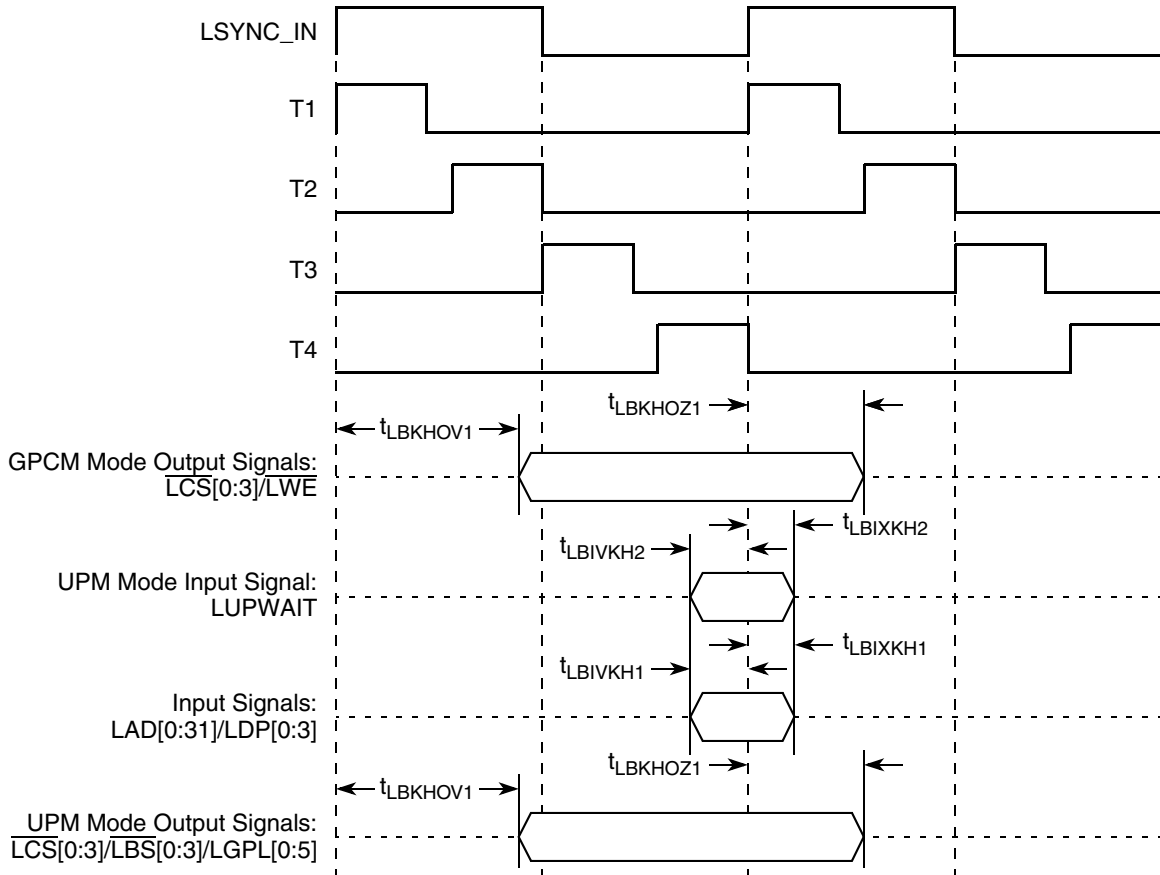


Figure 22. Local Bus Signals, GPCM/UPM Signals for LCCR[CLKDIV] = 4 (DLL Enabled)

11 JTAG

This section describes the DC and AC electrical specifications for the IEEE Std. 1149.1 (JTAG) interface of the MPC8343EA.

11.1 JTAG DC Electrical Characteristics

Table 36 provides the DC electrical characteristics for the IEEE Std. 1149.1 (JTAG) interface of the MPC8343EA.

Table 36. JTAG Interface DC Electrical Characteristics

Parameter	Symbol	Condition	Min	Max	Unit
Input high voltage	V_{IH}	—	$OV_{DD} - 0.3$	$OV_{DD} + 0.3$	V
Input low voltage	V_{IL}	—	-0.3	0.8	V
Input current	I_{IN}	—	—	±5	μA
Output high voltage	V_{OH}	$I_{OH} = -8.0 \text{ mA}$	2.4	—	V

Table 39. I²C AC Electrical Specifications (continued)

Parameter	Symbol ¹	Min	Max	Unit
Fall time of both SDA and SCL signals ⁵	t_{I2CF}	—	300	ns
Setup time for STOP condition	t_{I2PVKH}	0.6	—	μ s
Bus free time between a STOP and START condition	t_{I2KHDX}	1.3	—	μ s
Noise margin at the LOW level for each connected device (including hysteresis)	V_{NL}	$0.1 \times OV_{DD}$	—	V
Noise margin at the HIGH level for each connected device (including hysteresis)	V_{NH}	$0.2 \times OV_{DD}$	—	V

Notes:

1. The symbols for timing specifications follow the pattern of $t_{(first\ two\ letters\ of\ functional\ block)(signal)(state)(reference)(state)}$ for inputs and $t_{(first\ two\ letters\ of\ functional\ block)(reference)(state)(signal)(state)}$ for outputs. For example, t_{I2DVKH} symbolizes I²C timing (I2) with respect to the time data input signals (D) reach the valid state (V) relative to the t_{I2C} clock reference (K) going to the high (H) state or setup time. Also, t_{I2SXKL} symbolizes I²C timing (I2) for the time that the data with respect to the start condition (S) goes invalid (X) relative to the t_{I2C} clock reference (K) going to the low (L) state or hold time. Also, t_{I2PVKH} symbolizes I²C timing (I2) for the time that the data with respect to the stop condition (P) reaches the valid state (V) relative to the t_{I2C} clock reference (K) going to the high (H) state or setup time. For rise and fall times, the latter convention is used with the appropriate letter: R (rise) or F (fall).
2. The device provides a hold time of at least 300 ns for the SDA signal (referred to the $V_{IH(min)}$ of the SCL signal) to bridge the undefined region of the falling edge of SCL.
3. The maximum t_{I2DVKH} must be met only if the device does not stretch the LOW period (t_{I2CL}) of the SCL signal.
4. C_B = capacitance of one bus line in pF.
- 5.)The device does not follow the "I²C-BUS Specifications" version 2.1 regarding the t_{I2CF} AC parameter.

Figure 28 provides the AC test load for the I²C.

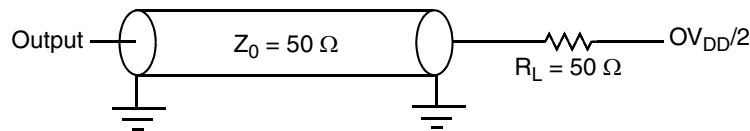

Figure 28. I²C AC Test Load

Figure 29 shows the AC timing diagram for the I²C bus.

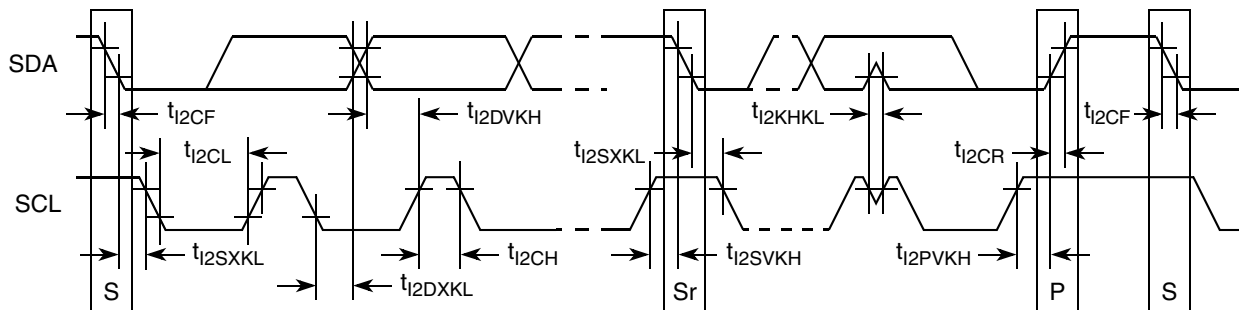

Figure 29. I²C Bus AC Timing Diagram

Figure 31 shows the PCI input AC timing diagram.

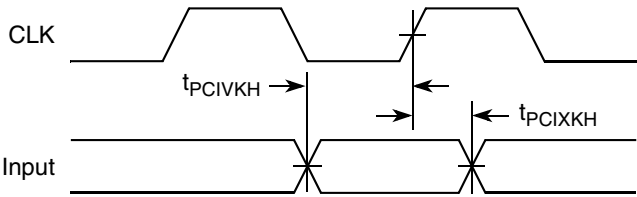


Figure 31. PCI Input AC Timing Diagram

Figure 32 shows the PCI output AC timing diagram.

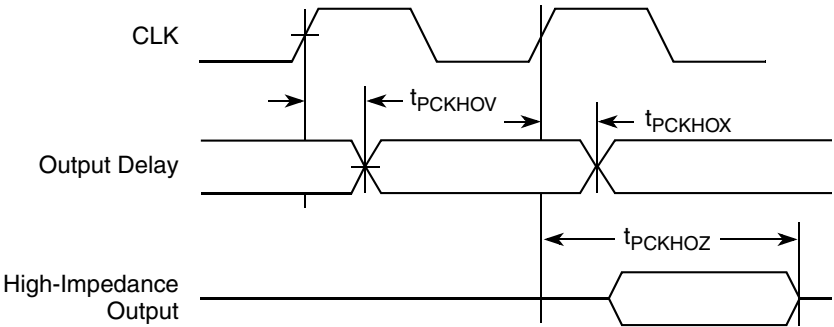


Figure 32. PCI Output AC Timing Diagram

14 Timers

This section describes the DC and AC electrical specifications for the timers.

14.1 Timer DC Electrical Characteristics

Table 43 provides the DC electrical characteristics for the MPC8343EA timer pins, including T_{IN} , \overline{TOUT} , \overline{TGATE} , and RTC_CLK .

Table 43. Timer DC Electrical Characteristics

Parameter	Symbol	Condition	Min	Max	Unit
Input high voltage	V_{IH}	—	2.0	$OV_{DD} + 0.3$	V
Input low voltage	V_{IL}	—	-0.3	0.8	V
Input current	I_{IN}	—	—	± 5	μA
Output high voltage	V_{OH}	$I_{OH} = -8.0 \text{ mA}$	2.4	—	V
Output low voltage	V_{OL}	$I_{OL} = 8.0 \text{ mA}$	—	0.5	V
Output low voltage	V_{OL}	$I_{OL} = 3.2 \text{ mA}$	—	0.4	V

16 IPIC

This section describes the DC and AC electrical specifications for the external interrupt pins.

16.1 IPIC DC Electrical Characteristics

Table 47 provides the DC electrical characteristics for the external interrupt pins.

Table 47. IPIC DC Electrical Characteristics¹

Parameter	Symbol	Condition	Min	Max	Unit	Notes
Input high voltage	V_{IH}	—	2.0	$OV_{DD} + 0.3$	V	—
Input low voltage	V_{IL}	—	−0.3	0.8	V	—
Input current	I_{IN}	—	—	±5	μA	—
Output low voltage	V_{OL}	$I_{OL} = 8.0 \text{ mA}$	—	0.5	V	2
Output low voltage	V_{OL}	$I_{OL} = 3.2 \text{ mA}$	—	0.4	V	2

Notes:

1. This table applies for pins $\overline{IRQ}[0:7]$, $\overline{IRQ_OUT}$, and $\overline{MCP_OUT}$.
2. $\overline{IRQ_OUT}$ and $\overline{MCP_OUT}$ are open-drain pins; thus V_{OH} is not relevant for those pins.

16.2 IPIC AC Timing Specifications

Table 48 provides the IPIC input and output AC timing specifications.

Table 48. IPIC Input AC Timing Specifications¹

Parameter	Symbol ²	Min	Unit
IPIC inputs—minimum pulse width	t_{PICWID}	20	ns

Notes:

1. Input specifications are measured at the 50 percent level of the IPIC input signals. Timings are measured at the pin.
2. IPIC inputs and outputs are asynchronous to any visible clock. IPIC outputs should be synchronized before use by external synchronous logic. IPIC inputs must be valid for at least t_{PICWID} ns to ensure proper operation in edge triggered mode.

17 SPI

This section describes the SPI DC and AC electrical specifications.

17.1 SPI DC Electrical Characteristics

Table 49 provides the SPI DC electrical characteristics.

Table 49. SPI DC Electrical Characteristics

Parameter	Symbol	Condition	Min	Max	Unit
Input high voltage	V_{IH}	—	2.0	$OV_{DD} + 0.3$	V
Input low voltage	V_{IL}	—	−0.3	0.8	V

Figure 34 and Figure 35 represent the AC timings from Table 50. Note that although the specifications generally reference the rising edge of the clock, these AC timing diagrams also apply when the falling edge is the active edge.

Figure 34 shows the SPI timings in slave mode (external clock).

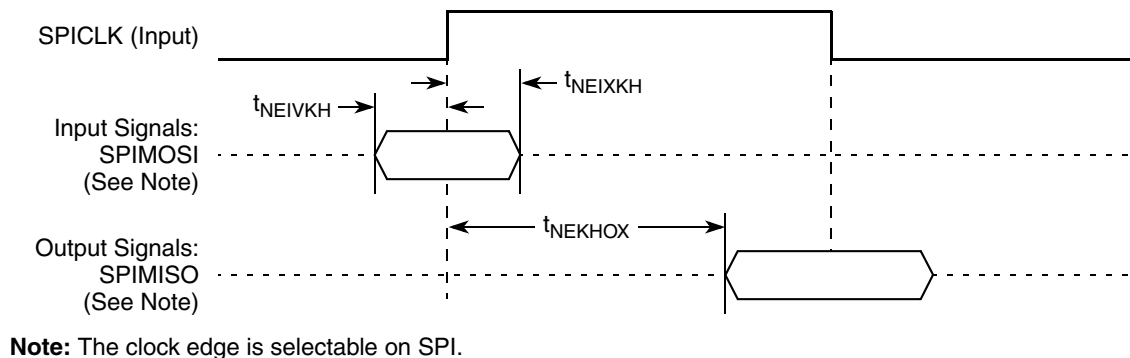


Figure 34. SPI AC Timing in Slave Mode (External Clock) Diagram

Figure 35 shows the SPI timings in master mode (internal clock).

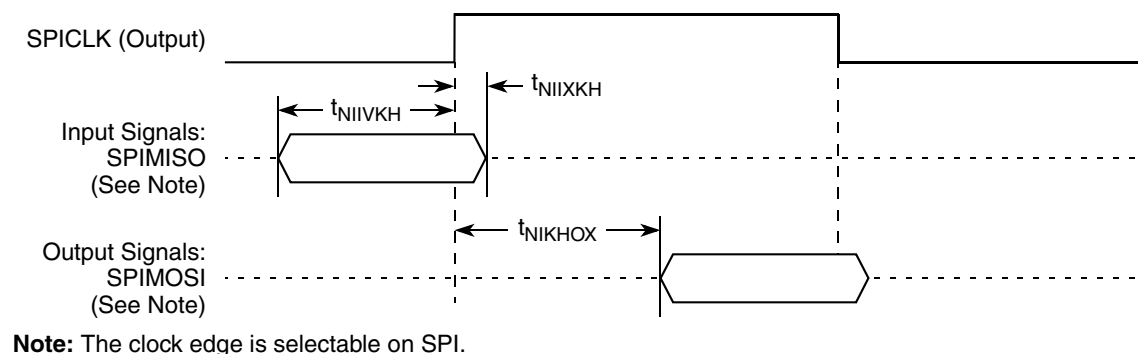


Figure 35. SPI AC Timing in Master Mode (Internal Clock) Diagram

18 Package and Pin Listings

This section details package parameters, pin assignments, and dimensions. The MPC8343EA is available in a plastic ball grid array (PBGA). See Section 18.1, “Package Parameters for the MPC8343EA PBGA,” and Section 18.2, “Mechanical Dimensions for the MPC8343EA PBGA.”

18.1 Package Parameters for the MPC8343EA PBGA

The package parameters are as provided in the following list. The package type is 29 mm × 29 mm, 620 plastic ball grid array (PBGA).

Package outline	29 mm × 29 mm
Interconnects	620
Pitch	1.00 mm
Module height (maximum)	2.46 mm

Table 51. MPC8343EA (PBGA) Pinout Listing (continued)

Signal	Package Pin Number	Pin Type	Power Supply	Notes
MECC[0:4]/MSRCID[0:4]	AG13, AE14, AH12, AH10, AE15	I/O	GV _{DD}	—
MECC[5]/MDVAL	AH14	I/O	GV _{DD}	—
MECC[6:7]	AE13, AH11	I/O	GV _{DD}	—
MDM[0:3]	AG28, AG24, AF20, AG17	O	GV _{DD}	—
MDM[8]	AG12	O	GV _{DD}	—
MDQS[0:3]	AE27, AE26, AE20, AH18	I/O	GV _{DD}	—
MDQS[8]	AH13	I/O	GV _{DD}	—
MBA[0:1]	AF10, AF11	O	GV _{DD}	—
MA[0:14]	AF13, AF15, AG16, AD16, AF17, AH20, AH19, AH21, AD18, AG21, AD13, AF21, AF22, AE1, AA5	O	GV _{DD}	—
$\overline{\text{MWE}}$	AD10	O	GV _{DD}	—
$\overline{\text{MRAS}}$	AF7	O	GV _{DD}	—
$\overline{\text{MCAS}}$	AG6	O	GV _{DD}	—
$\overline{\text{MCS}}[0:3]$	AE7, AH7, AH4, AF2	O	GV _{DD}	—
MCKE[0:1]	AG23, AH23	O	GV _{DD}	3
MCK[0:3]	AH15, AE24, AE2, AF14	O	GV _{DD}	—
$\overline{\text{MCK}}[0:3]$	AG15, AD23, AE3, AG14	O	GV _{DD}	—
MODT[0:3]	AG5, AD4, AH6, AF4	O	GV _{DD}	—
MBA[2]	AD22	O	GV _{DD}	—
MDIC0	AG11	I/O	—	9
MDIC1	AF12	I/O	—	9
Local Bus Controller Interface				
LAD[0:31]	T4, T5, T1, R2, R3, T2, R1, R4, P1, P2, P3, P4, N1, N4, N2, N3, M1, M2, M3, N5, M4, L1, L2, L3, K1, M5, K2, K3, J1, J2, L5, J3	I/O	OV _{DD}	—
LDP[0]/CKSTOP_OUT	H1	I/O	OV _{DD}	—
LDP[1]/CKSTOP_IN	K5	I/O	OV _{DD}	—
LDP[2]/LCS[4]	H2	I/O	OV _{DD}	—
LDP[3]/LCS[5]	G1	I/O	OV _{DD}	—
LA[27:31]	J4, H3, G2, F1, G3	O	OV _{DD}	—
$\overline{\text{LCS}}[0:3]$	J5, H4, F2, E1	O	OV _{DD}	—
$\overline{\text{LWE}}[0:3]/\text{LSDDQM}[0:3]/\overline{\text{LBS}}[0:3]$	F3, G4, D1, E2	O	OV _{DD}	—

Table 51. MPC8343EA (PBGA) Pinout Listing (continued)

Signal	Package Pin Number	Pin Type	Power Supply	Notes
LBCTL	H5	O	OV _{DD}	—
LALE	E3	O	OV _{DD}	—
LGPL0/LSDA10/cfg_reset_source0	F4	I/O	OV _{DD}	—
LGPL1/LSDWE/cfg_reset_source1	D2	I/O	OV _{DD}	—
LGPL2/LSDRAS/LOE	C1	O	OV _{DD}	—
LGPL3/LSDCAS/cfg_reset_source2	C2	I/O	OV _{DD}	—
LGPL4/LGTA/LUPWAIT/LPBSE	C3	I/O	OV _{DD}	12
LGPL5/cfg_clkin_div	B3	I/O	OV _{DD}	—
LCKE	E4	O	OV _{DD}	—
LCLK[0:2]	D4, A3, C4	O	OV _{DD}	—
LSYNC_OUT	U3	O	OV _{DD}	—
LSYNC_IN	Y2	I	OV _{DD}	—
General Purpose I/O Timers				
GPIO1[0]/DMA_DREQ0/GTM1_TIN1/ GTM2_TIN2	D27	I/O	OV _{DD}	—
GPIO1[1]/DMA_DACK0/GTM1_TGATE1/ GTM2_TGATE2	E26	I/O	OV _{DD}	—
GPIO1[2]/DMA_DDONE0/ GTM1_TOUT1	D28	I/O	OV _{DD}	—
GPIO1[3]/DMA_DREQ1/GTM1_TIN2/ GTM2_TIN1	G25	I/O	OV _{DD}	—
GPIO1[4]/DMA_DACK1/ GTM1_TGATE2/GTM2_TGATE1	J24	I/O	OV _{DD}	—
GPIO1[5]/DMA_DDONE1/ GTM1_TOUT2/GTM2_TOUT1	F26	I/O	OV _{DD}	—
GPIO1[6]/DMA_DREQ2/GTM1_TIN3/ GTM2_TIN4	E27	I/O	OV _{DD}	—
GPIO1[7]/DMA_DACK2/GTM1_TGATE3/ GTM2_TGATE4	E28	I/O	OV _{DD}	—
GPIO1[8]/DMA_DDONE2/ GTM1_TOUT3	H25	I/O	OV _{DD}	—
GPIO1[9]/DMA_DREQ3/GTM1_TIN4/ GTM2_TIN3	F27	I/O	OV _{DD}	—
GPIO1[10]/DMA_DACK3/ GTM1_TGATE4/GTM2_TGATE3	K24	I/O	OV _{DD}	—
GPIO1[11]/DMA_DDONE3/ GTM1_TOUT4/GTM2_TOUT3	G26	I/O	OV _{DD}	—

Table 51. MPC8343EA (PBGA) Pinout Listing (continued)

Signal	Package Pin Number	Pin Type	Power Supply	Notes
USB				
DR_D0_ENABLEN	C28	I/O	OV _{DD}	—
DR_D1_SER_TXD	F25	I/O	OV _{DD}	—
DR_D2_VMO_SE0	B28	I/O	OV _{DD}	—
DR_D3_SPEED	C27	I/O	OV _{DD}	—
DR_D4_DP	D26	I/O	OV _{DD}	—
DR_D5_DM	E25	I/O	OV _{DD}	—
DR_D6_SER_RCV	C26	I/O	OV _{DD}	—
DR_D7_DRVVBUS	D25	I/O	OV _{DD}	—
DR_SESS_VLD_NXT	B26	I	OV _{DD}	—
DR_XCVR_SEL_DPPULLUP	E24	I/O	OV _{DD}	—
DR_STP_SUSPEND	A27	O	OV _{DD}	—
DR_RX_ERROR_PWRFAULT	C25	I	OV _{DD}	—
DR_TX_VALID_PCTL0	A26	O	OV _{DD}	—
DR_TX_VALIDH_PCTL1	B25	O	OV _{DD}	—
DR_CLK	A25	I	OV _{DD}	—
Programmable Interrupt Controller				
MCP_OUT	E8	O	OV _{DD}	2
IRQ0/MCP_IN/GPIO2[12]	J28	I/O	OV _{DD}	—
IRQ[1:5]/GPIO2[13:17]	K25, J25, H26, L24, G27	I/O	OV _{DD}	—
IRQ[6]/GPIO2[18]/CKSTOP_OUT	G28	I/O	OV _{DD}	—
IRQ[7]/GPIO2[19]/CKSTOP_IN	J26	I/O	OV _{DD}	—
Ethernet Management Interface				
EC_MDC	Y24	O	LV _{DD1}	—
EC_MDIO	Y25	I/O	LV _{DD1}	11
Gigabit Reference Clock				
EC_GTX_CLK125	Y26	I	LV _{DD1}	—
Three-Speed Ethernet Controller (Gigabit Ethernet 1)				
TSEC1_COL/GPIO2[20]	M26	I/O	OV _{DD}	—
TSEC1_CRS/GPIO2[21]	U25	I/O	LV _{DD1}	—
TSEC1_GTX_CLK	V24	O	LV _{DD1}	3
TSEC1_RX_CLK	U26	I	LV _{DD1}	—

Table 51. MPC8343EA (PBGA) Pinout Listing (continued)

Signal	Package Pin Number	Pin Type	Power Supply	Notes
TSEC1_RX_DV	U24	I	LV _{DD1}	—
TSEC1_RX_ER/GPIO2[26]	L28	I/O	OV _{DD}	—
TSEC1_RXD[3:0]	W26, W24, Y28, Y27	I	LV _{DD1}	—
TSEC1_TX_CLK	N25	I	OV _{DD}	—
TSEC1_TXD[3:0]	V28, V27, V26, W28	O	LV _{DD1}	10
TSEC1_TX_EN	W27	O	LV _{DD1}	—
TSEC1_TX_ER/GPIO2[31]	N24	I/O	OV _{DD}	—
Three-Speed Ethernet Controller (Gigabit Ethernet 2)				
TSEC2_COL/GPIO1[21]	P28	I/O	OV _{DD}	—
TSEC2_CRS/GPIO1[22]	AC28	I/O	LV _{DD2}	—
TSEC2_GTX_CLK	AC27	O	LV _{DD2}	—
TSEC2_RX_CLK	AB25	I	LV _{DD2}	—
TSEC2_RX_DV/GPIO1[23]	AC26	I/O	LV _{DD2}	—
TSEC2_RXD[3:0]/GPIO1[13:16]	AA25, AA26, AA27, AA28	I/O	LV _{DD2}	—
TSEC2_RX_ER/GPIO1[25]	R25	I/O	OV _{DD}	—
TSEC2_TXD[3:0]/GPIO1[17:20]	AB26, AB27, AA24, AB28	I/O	LV _{DD2}	—
TSEC2_TX_ER/GPIO1[24]	R27	I/O	OV _{DD}	—
TSEC2_TX_EN/GPIO1[12]	AD28	I/O	LV _{DD2}	3
TSEC2_TX_CLK/GPIO1[30]	R26	I/O	OV _{DD}	—
UART				
UART_SOUT[1:2]/MSRCID[0:1]/LSRCID[0:1]	B4, A4	O	OV _{DD}	—
UART_SIN[1:2]/MSRCID[2:3]/LSRCID[2:3]	D5, C5	I/O	OV _{DD}	—
UART_CTS[1]/MSRCID4/LSRCID4	B5	I/O	OV _{DD}	—
UART_CTS[2]/MDVAL/LDVAL	A5	I/O	OV _{DD}	—
UART_RTS[1:2]	D6, C6	O	OV _{DD}	—
I²C interface				
IIC1_SDA	E5	I/O	OV _{DD}	2
IIC1_SCL	A6	I/O	OV _{DD}	2
IIC2_SDA	B6	I/O	OV _{DD}	2
IIC2_SCL	E7	I/O	OV _{DD}	2

Table 51. MPC8343EA (PBGA) Pinout Listing (continued)

Signal	Package Pin Number	Pin Type	Power Supply	Notes
Power and Ground Signals				
AV _{DD1}	C15	Power for e300 PLL (1.2 V)	AV _{DD1}	—
AV _{DD2}	U1	Power for system PLL (1.2 V)	AV _{DD2}	—
AV _{DD3}	AF9	Power for DDR DLL (1.2 V)	—	—
AV _{DD4}	U2	Power for LBIU DLL (1.2 V)	AV _{DD4}	—
GND	A2, B1, B2, D10, D18, E6, E14, E22, F9, F12, F15, F18, F21, F24, G5, H6, J23, L4, L6, L12, L13, L14, L15, L16, L17, M11, M12, M13, M14, M15, M16, M17, M18, M23, N11, N12, N13, N14, N15, N16, N17, N18, P6, P11, P12, P13, P14, P15, P16, P17, P18, P24, R5, R23, R11, R12, R13, R14, R15, R16, R17, R18, T11, T12, T13, T14, T15, T16, T17, T18, U6, U11, U12, U13, U14, U15, U16, U17, U18, V12, V13, V14, V15, V16, V17, V23, V25, W4, Y6, AA23, AB24, AC5, AC8, AC11, AC14, AC17, AC20, AD9, AD15, AD21, AE12, AE18, AF3, AF26	—	—	—
GV _{DD}	U9, V9, W10, W19, Y11, Y12, Y14, Y15, Y17, Y18, AA6, AB5, AC9, AC12, AC15, AC18, AC21, AC24, AD6, AD8, AD14, AD20, AE5, AE11, AE17, AG2, AG27	Power for DDR DRAM I/O voltage (2.5 V)	GV _{DD}	—
LV _{DD1}	U20, W25	Power for three speed Ethernet #1 and for Ethernet management interface I/O (2.5V, 3.3V)	LV _{DD1}	—
LV _{DD2}	V20, Y23	Power for three speed Ethernet #2 I/O (2.5 V, 3.3 V)	LV _{DD2}	—
V _{DD}	J11, J12, J15, K10, K11, K12, K13, K14, K15, K16, K17, K18, K19, L10, L11, L18, L19, M10, M19, N10, N19, P9, P10, P19, R10, R19, R20, T10, T19, U10, U19, V10, V11, V18, V19, W11, W12, W13, W14, W15, W16, W17, W18	Power for core (1.2 V)	V _{DD}	—

Table 58. Suggested PLL Configurations (continued)

Ref No. ¹	RCWL		266 MHz Device			333 MHz Device			400 MHz Device		
	SPMF	CORE PLL	Input Clock Freq (MHz) ²	CSB Freq (MHz)	Core Freq (MHz)	Input Clock Freq (MHz) ²	CSB Freq (MHz)	Core Freq (MHz)	Input Clock Freq (MHz) ²	CSB Freq (MHz)	Core Freq (MHz)
326	0011	0100110	—			33	100	300	33	100	300
623	0110	0100011	—			33	200	300	33	200	300
922	1001	0100010	—			33	300	300	33	300	300
425	0100	0100101	—			33	133	333	33	133	333
524	0101	0100100	—			33	166	333	33	166	333
A22	1010	0100010	—			33	333	333	33	333	333
723	0111	0100011	—			—			33	233	350
604	0110	0000100	—			—			33	200	400
624	0110	0100100	—			—			33	200	400
823	1000	0100011	—			—			33	266	400
66 MHz CLKIN/PCI_CLK Options											
242	0010	1000010	66	133	133	66	133	133	66	133	133
322	0011	0100010	66	200	200	66	200	200	66	200	200
224	0010	0100100	66	133	266	66	133	266	66	133	266
422	0100	0100010	66	266	266	66	266	266	66	266	266
323	0011	0100011	—			66	200	300	66	200	300
223	0010	0100101	—			66	133	333	66	133	333
522	0101	0100010	—			66	333	333	66	333	333
304	0011	0000100	—			—			66	200	400
324	0011	0100100	—			—			66	200	400
403	0100	0000011	—			—			66	266	400
423	0100	0100011	—			—			66	266	400

¹ The PLL configuration reference number is the hexadecimal representation of RCWL, bits 4–15 associated with the SPMF and COREPLL settings given in the table.

² The input clock is CLKIN for PCI host mode or PCI_CLK for PCI agent mode.

$R_{\theta JC}$ = junction-to-case thermal resistance ($^{\circ}\text{C}/\text{W}$)

P_D = power dissipation (W)

21 System Design Information

This section provides electrical and thermal design recommendations for successful application of the MPC8343EA.

21.1 System Clocking

The MPC8343EA includes two PLLs:

1. The platform PLL generates the platform clock from the externally supplied CLKIN input. The frequency ratio between the platform and CLKIN is selected using the platform PLL ratio configuration bits as described in [Section 19.1, “System PLL Configuration.”](#)
2. The e300 core PLL generates the core clock as a slave to the platform clock. The frequency ratio between the e300 core clock and the platform clock is selected using the e300 PLL ratio configuration bits as described in [Section 19.2, “Core PLL Configuration.”](#)

21.2 PLL Power Supply Filtering

Each PLL gets power through independent power supply pins (AV_{DD1} , AV_{DD2} , respectively). The AV_{DD} level should always equal to V_{DD} , and preferably these voltages are derived directly from V_{DD} through a low frequency filter scheme.

There are a number of ways to provide power reliably to the PLLs, but the recommended solution is to provide four independent filter circuits as illustrated in [Figure 38](#), one to each of the four AV_{DD} pins. Independent filters to each PLL reduce the opportunity to cause noise injection from one PLL to the other.

The circuit filters noise in the PLL resonant frequency range from 500 kHz to 10 MHz. It should be built with surface mount capacitors with minimum effective series inductance (ESL). Consistent with the recommendations of Dr. Howard Johnson in *High Speed Digital Design: A Handbook of Black Magic* (Prentice Hall, 1993), multiple small capacitors of equal value are recommended over a single large value capacitor.

To minimize noise coupled from nearby circuits, each circuit should be placed as closely as possible to the specific AV_{DD} pin being supplied. It should be possible to route directly from the capacitors to the AV_{DD} pin, which is on the periphery of package, without the inductance of vias.

[Figure 38](#) shows the PLL power supply filter circuit.

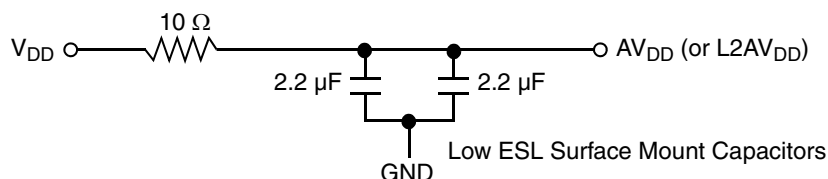


Figure 38. PLL Power Supply Filter Circuit

Table 64. Document Revision History (continued)

Rev. Number	Date	Substantive Change(s)
3	11/2006	<ul style="list-style-type: none"> Updated note in introduction. In the features list in Section 1, "Overview," updated DDR data rate to show 266 MHz for PBGA parts for all silicon revisions. In Table 57, "Suggested PLL Configurations," added the following row: Ref No: 823, SPMF: 1000, Core PLL: 0100011, 400-MHz Device Input Clock Freq: 33, CSB Freq: 266, and Core Freq: 400. In Section 23, "Ordering Information," replicated note from document introduction.
2	8/2006	<ul style="list-style-type: none"> Changed all references to revision 2.0 silicon to revision 3.0 silicon. Changed number of general purpose parallel I/O pins to 39 in Section 1, "Overview." Changed VIH minimum value in Table 35, "JTAG Interface DC Electrical Characteristics," to $OV_{DD} - 0.3$. In Table 40, "PCI DC Electrical Characteristics," changed high-level input voltage values to min = 2 and max = $OV_{DD} + 0.3$; changed low-level input voltage values to min = (-0.3) and max = 0.8. In Table 44, "PCI DC Electrical Characteristics," changed high-level input voltage values to min = 2 and max = $OV_{DD} + 0.3$; changed low-level input voltage values to min = (-0.3) and max = 0.8. In Table 44, "PCI DC Electrical Characteristics," changed high-level input voltage values to min = 2 and max = $OV_{DD} + 0.3$; changed low-level input voltage values to min = (-0.3) and max = 0.8. Updated DDR2 I/O power values in Table 5, "MPC8347EA Typical I/O Power Dissipation."
1	4/2006	<ul style="list-style-type: none"> Removed Table 20, "Timing Parameters for DDR2-400." Changed ADDR/CMD to ADDR/CMD/MODT in Table 9, "DDR and DDR2 SDRAM Output AC Timing Specifications," rows 2 and 3, and in Figure 2, "DDR SDRAM Output Timing Diagram." Changed Min and Max values for V_{IH} and V_{IL} in Table 40Table 44, "PCI DC Electrical Characteristics." In Table 58, "MPC8343EA (PBGA) Pinout Listing," and Table 52, "MPC8347EA (PBGA) Pinout Listing," modified rows for MDICO and MDIC1 signals and added note 'It is recommended that MDICO be tied to GRD using an 18 Ω resistor and MCIC1 be tied to DDR power using an 18 Ω resistor.' Table 58, "MPC8343EA (PBGA) Pinout Listing," in row AVDD3 changed power supply from "AVDD3" to '—.'
0	3/2006	Initial public release